Notice of Allowability	Application No.	Applicant(s)
	10/814,867	BERNARD ET AL.
	Examiner	Art Unit
	My-Trang N. Ton	2816
The MAILING DATE of this communication appe All claims being allowable, PROSECUTION ON THE MERITS IS (herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIG	ars on the cover sheet with the co (OR REMAINS) CLOSED in this applied or other appropriate communication GHTS. This application is subject to	plication. If not included  will be mailed in due course. THIS
1. This communication is responsive to <u>Amdt. filed 6/9/06</u> .		
2. $\boxtimes$ The allowed claim(s) is/are <u>1-91 and 93-100</u> .		
<ol> <li>Acknowledgment is made of a claim for foreign priority un</li> <li>a) All b) Some* c) None of the:</li> <li>1. Certified copies of the priority documents have</li> <li>2. Certified copies of the priority documents have</li> <li>3. Copies of the certified copies of the priority documents have International Bureau (PCT Rule 17.2(a)).</li> </ol> * Certified copies not received:	been received. been received in Application No	
Applicant has THREE MONTHS FROM THE "MAILING DATE" of noted below. Failure to timely comply will result in ABANDONMI THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.	of this communication to file a reply ENT of this application.	complying with the requirements
<ol> <li>A SUBSTITUTE OATH OR DECLARATION must be submit INFORMAL PATENT APPLICATION (PTO-152) which give</li> </ol>	tted. Note the attached EXAMINER's reason(s) why the oath or declara	S AMENDMENT or NOTICE OF tion is deficient.
5. CORRECTED DRAWINGS ( as "replacement sheets") must	t be submitted.	
(a) including changes required by the Notice of Draftsperso		948) attached
1) hereto or 2) to Paper No./Mail Date		
(b) ☐ including changes required by the attached Examiner's Paper No./Mail Date	Amendment / Comment or in the C	office action of
Identifying indicia such as the application number (see 37 CFR 1, each sheet. Replacement sheet(s) should be labeled as such in the	84(c)) should be written on the drawir ne header according to 37 CFR 1.121(c	ngs in the front (not the back) of d).
<ol> <li>DEPOSIT OF and/or INFORMATION about the depos attached Examiner's comment regarding REQUIREMENT F</li> </ol>	sit of BIOLOGICAL MATERIAL n FOR THE DEPOSIT OF BIOLOGICA	nust be submitted. Note the AL MATERIAL.
Attachment(s)  1. Notice of References Cited (PTO-892)		atent Application (PTO-152)
2. Notice of Draftperson's Patent Drawing Review (PTO-948)	<ol> <li>Interview Summary Paper No./Mail Dat</li> </ol>	e
<ol> <li>Information Disclosure Statements (PTO-1449 or PTO/SB/08 Paper No./Mail Date 6/9/06</li> </ol>	3), 7. Examiner's Amendo	
4. ☐ Examiner's Comment Regarding Requirement for Deposit of Biological Material	8. ⊠ Examiner's Stateme	MY-TRANG NU TON PRIMARY EXAMINER

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## Reasons for allowance

The following is an examiner's statement of reasons for allowance:

1. As noted in the previous Office action, none of the prior art disclosed or suggested to show the particular structure and/or the particular operation recited in these claims namely: "a diode" in combination with "a first pFET", "a second pFET" and "a high-voltage MOS nFET" as recited in claims 1 and 62; "a diode" in combination with "a first pFET", "a second pFET", "a high-voltage MOS nFET", "a pull-up circuit" and "a capacitor" as recited in claim 8; "a diode" and "a high-voltage MOS nFET" in combination with "a first pFET", "a second pFET" and "a MOS nFET" as recited in claim 13; "a diode" and "a high-voltage MOS nFET" in combination with "a first pFET", "a second pFET", "a MOS nFET" and "a pull-up circuit" as recited in claim 22; "a diode" (or a first diode) in combination with "a first pFET", "a second pFET", "third pFET" and "a high-voltage MOS nFET" as recited in claims 31, 36 and 54; set-reset latch circuit" and "a first diode" in combination with "a first pFET", "a second pFET" and "a high-voltage MOS nFET" as recited in claim 41; "a first high-voltage nFET" and "a diode" in combination with "a first pFET", "a second pFET" and "a second high-voltage nFET" as recited in claim 68; "a first and a second high-voltage nFET" and "a first and second diodes" in combination with "a first and a second pFET" and "a third and a fourth pFET" as recited in claim 74; the combination of "a first and a second pFET", "a first circuit portion", "a second circuit portion", "a third and fourth pFET" and "a first and a second high-voltage circuit portion" as recited in claim 77; "first – second diodes" in combination with "first - fourth pFETs" and "a first and a second high-voltage circuit

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portion" as recited in claim 90; "a first and a second n-well diode", "a third and fourth pFET" and "a first and a second high-voltage circuit portion" in combination with "a first and a second pFET" as recited in claim 96.

2. The prior art references submitted by the applicant on IDS form received on 6/9/06 was reviewed and considered. However, these references still lack the combination limitations as cited in the claims. Therefore, the claims are patentably distinct over all these prior art references of record.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Any inquiry concerning this communication or earlier communications from the examiner should be directed to My-Trang N. Ton whose telephone number is 571-272-1754. The examiner can normally be reached on 7:00 a.m - 5:30 p.m.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Timothy Callahan can be reached on 571-272-1740. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

My-Trang N. Ton Primary Examiner Art Unit 2816

mylmongh

June 26, 2006